

**INTRODUCE:**

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

**FEATURES:**

1. Super small.
2. Middle current.
3. High frequency, Ultra fast recovery.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuum Have anticorrosion in the surface.

**APPLICATIONS:**

1. High voltage multiplier circuit
2. X-ray generator.
3. General purpose high voltage rectifier.
4. Other.

**MECHANICAL DATA:**

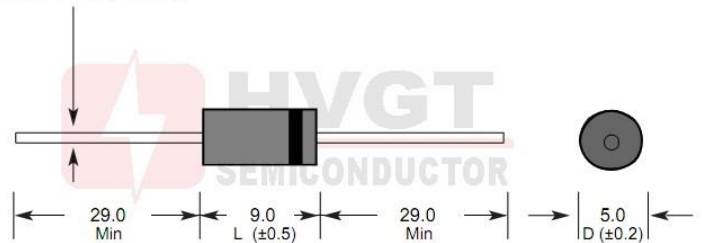
1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.1 grams (approx).

**SHAPE DISPLAY:**



**SIZE: (Unit:mm)** **HVGT NAME: DO-590**

**DO-590 Series**  
Lead Diameter 1.28 (±0.02)



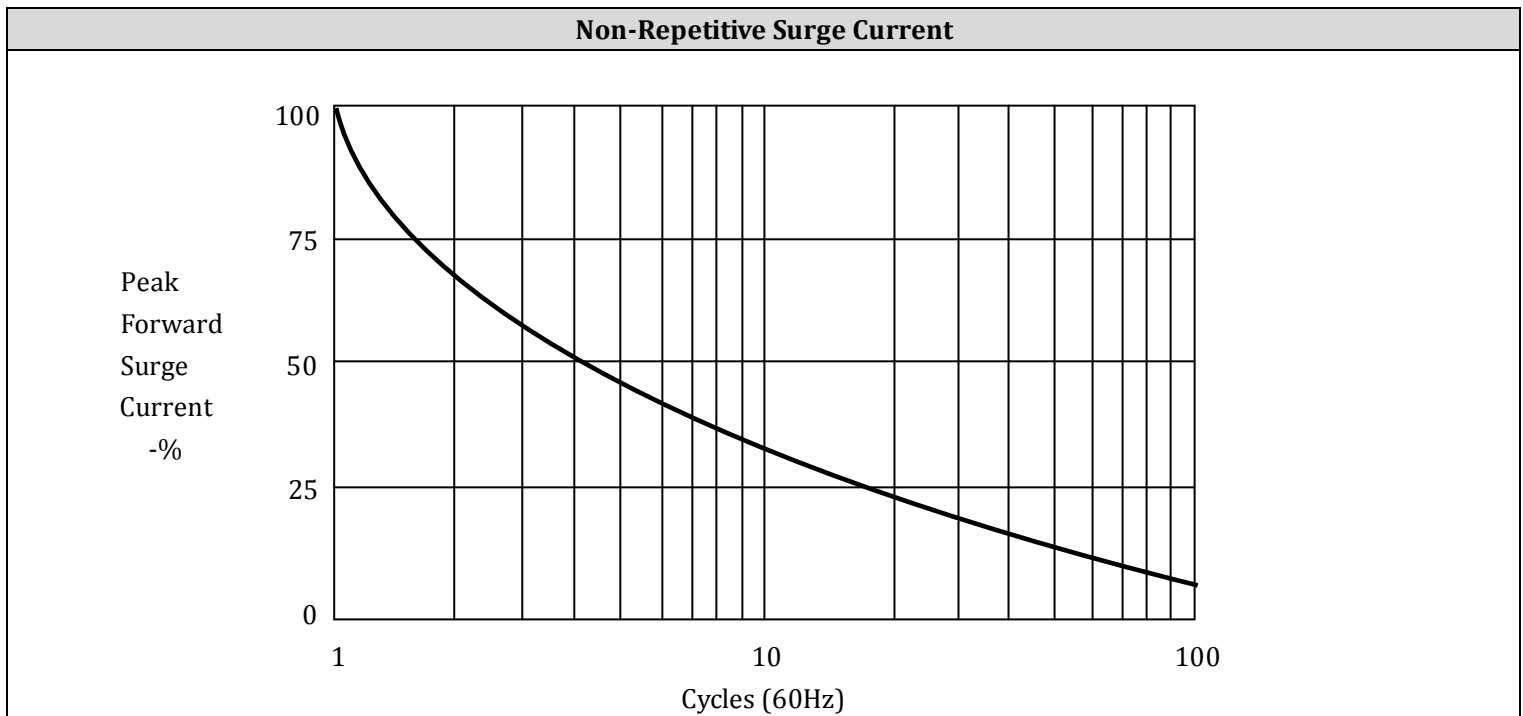
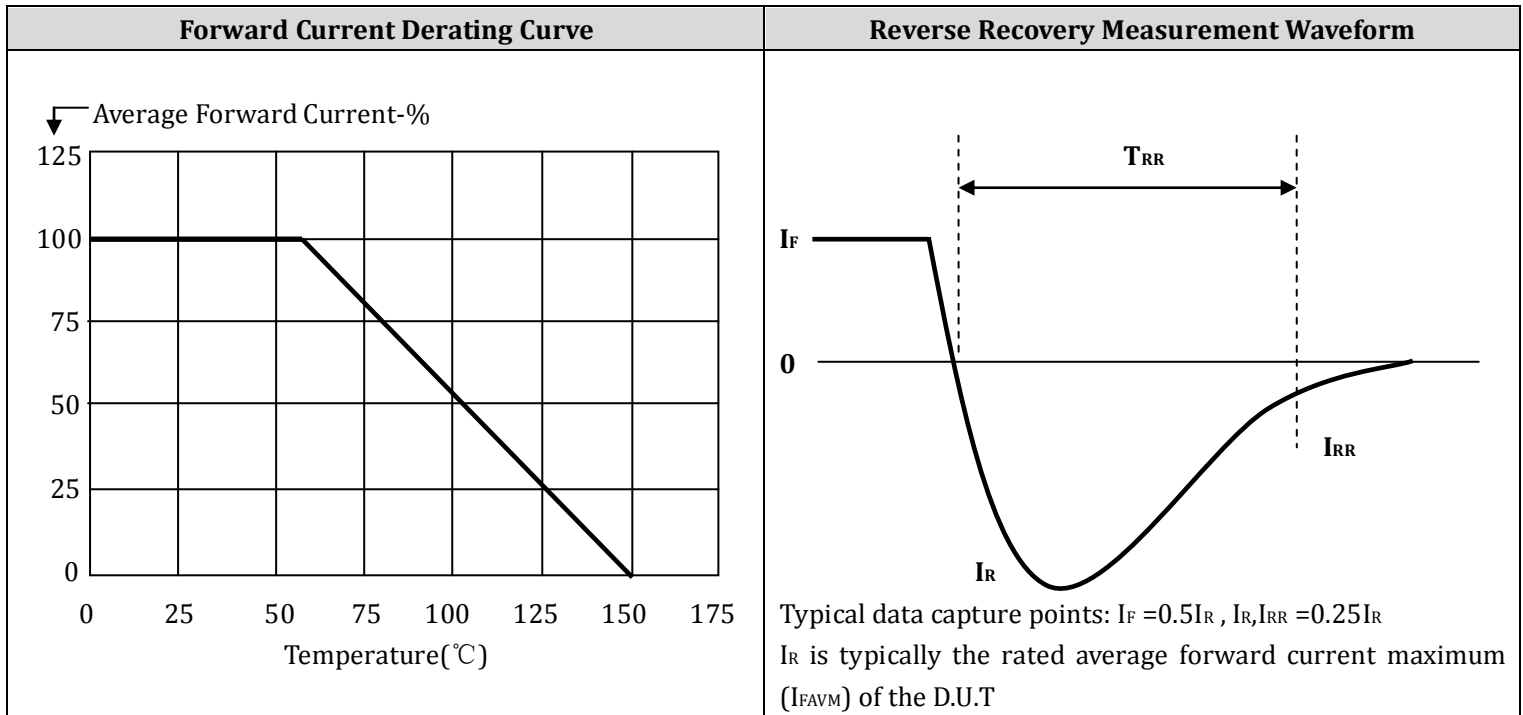
Unit:mm

**MAXIMUM RATINGS AND CHARACTERISTICS:** (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_A=25^{\circ}C$	8.0	kV
Non-Repetitive Peak Reverse Voltage	$V_{RSM}$	$T_A=25^{\circ}C$	10	kV
Average Forward Current Maximum	$I_{FAVM}$	$T_A=55^{\circ}C$	420	mA
		$T_{OIL}=55^{\circ}C$	500	mA
Non-Repetitive Forward Surge Current	$I_{FSM}$	$T_A=25^{\circ}C$ ; 60Hz Half-Sine Wave; 8.3ms	20	A
Junction Temperature	$T_J$		150	$^{\circ}C$
Allowable Operation Case Temperature	$T_C$		-40~+150	$^{\circ}C$
Storage Temperature	$T_{STG}$		-40~+150	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS:**  $T_A=25^{\circ}C$  (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	$V_{FM}$	at $25^{\circ}C$ ; at $I_{FAVM}$	12	V
Maximum Reverse Current	$I_{R1}$	at $25^{\circ}C$ ; at $V_{RRM}$	0.5	$\mu A$
	$I_{R2}$	at $125^{\circ}C$ ; at $V_{RRM}$	50	$\mu A$
Maximum Reverse Recovery Time	$T_{RR}$	at $25^{\circ}C$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$	40	nS
Junction Capacitance	$C_J$	at $25^{\circ}C$ ; $V_R=0V$ ; $f=1MHz$	7.5	pF



	Type	Code	Cathode Mark
<b>Marking</b>	UX-FBR8	UFBR8 HVGT	